

Quantum Partition Noise of photon excited electron-hole pairs

Is it possible to observe quantum partition noise
without net electron transport ?

Laure-Hélène Reydellet

CEA-Saclay
NanoElectronic group

Christian Glattli

CEA-Saclay / ENS-Paris
NanoElectronic group

Patrice Roche

CEA-Saclay
NanoElectronic group

Yong Jin

LPN-Marcoussis

Bernard Etienne

(ordinary) Transport Shot Noise

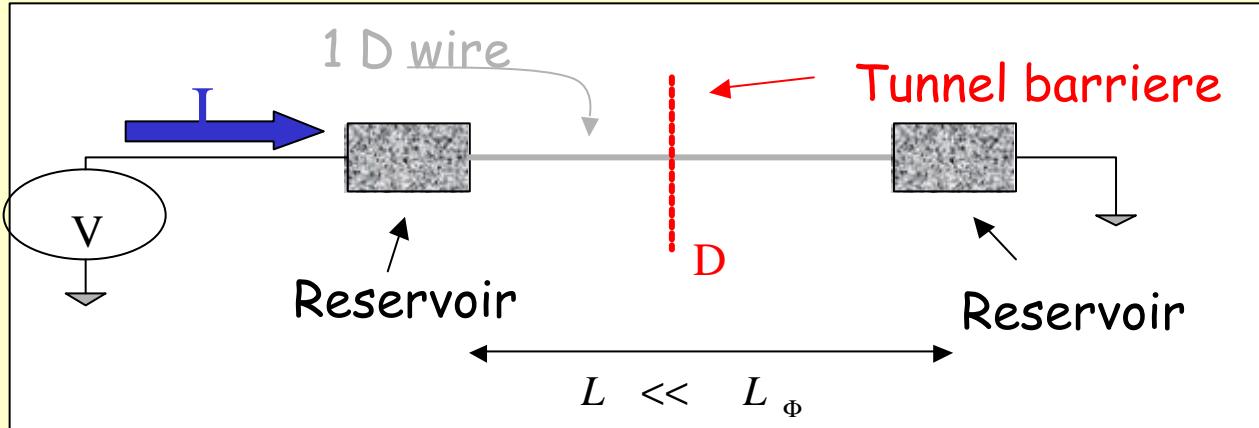
In general, shot noise requires **non-equilibrium** conditions.

In nearly all present works, non-equilibrium is provided by a **voltage bias**



Incoming current :

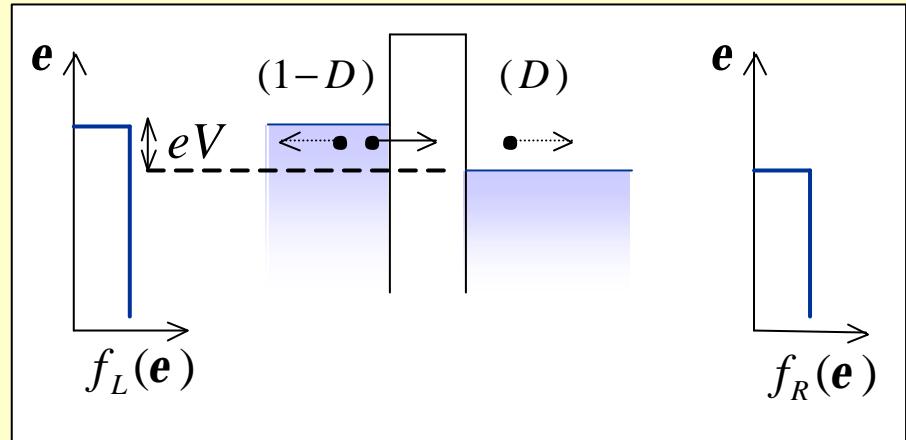
$$I_0 = e (eV / h)$$



Transmitted current :

$$I = D I_0 = D \frac{e^2}{h} V$$

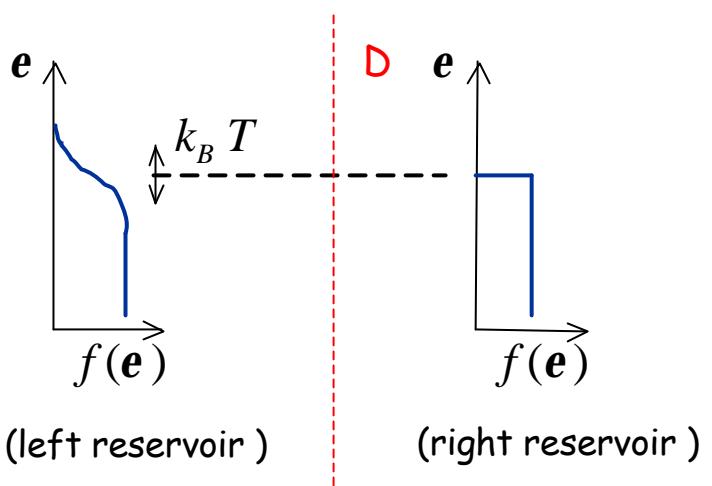
current shot noise power :



$$S_I = 2e I_0 D(1-D) = 2e I (1-D)$$

$$S_I(w) = \int \overline{I(t)I(t+\tau)} \cos(wt) dt$$

Other non-equilibrium cases are however possible while no electrons flow through the conductor (**non-transport shot noise**):

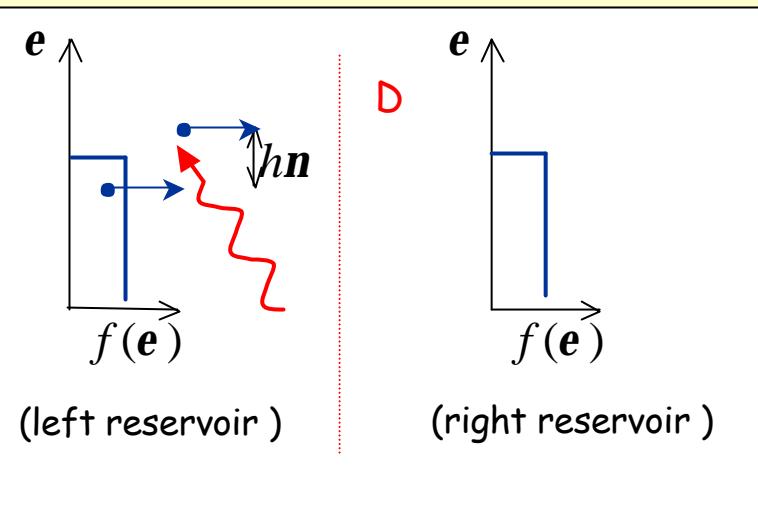


- heating one of the reservoirs.

[Sukhorukov and Loss PRB \(1999\)](#)

$$S_I = 2k_B T \frac{e^2}{h} [D^2 + 2\ln(2)D(1-D)]$$

(no measurements yet available)



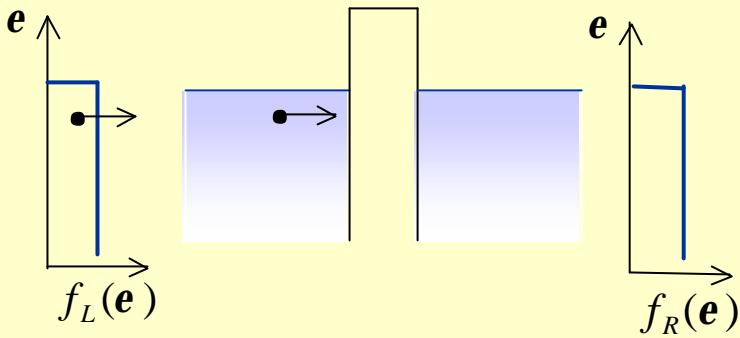
- coherent rf pumping of electron emitted from one side of the conductor.

(this presentation)

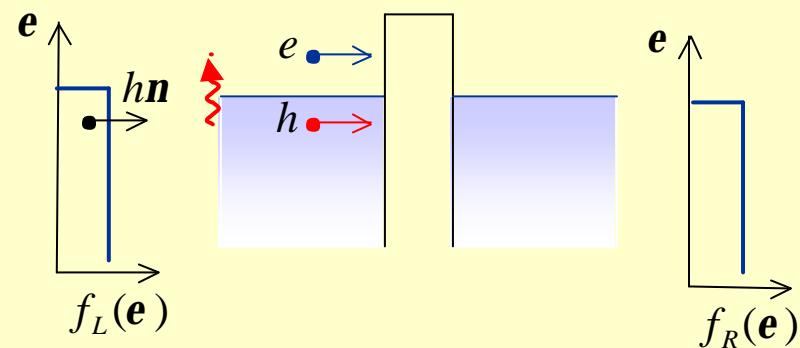
Partition noise of photon-created Electron-hole pairs (non-transport Shot Noise)

an incoming electron can be either

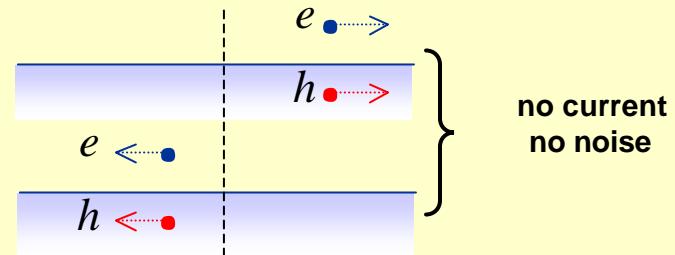
unpumped (prob. P_0)



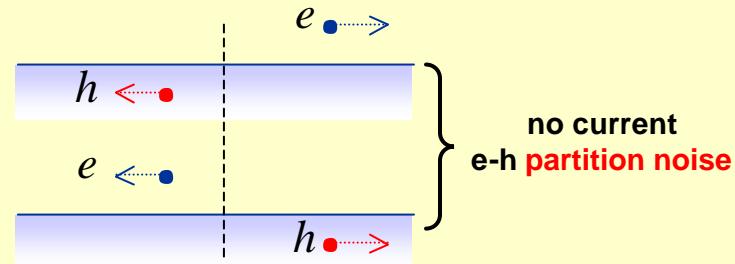
or pumped (prob. P_1)



unpumped electrons do not generate noise (ground state)



pumped electrons do generate noise as $e - h$ pairs are dissociated by the elastic scatter.

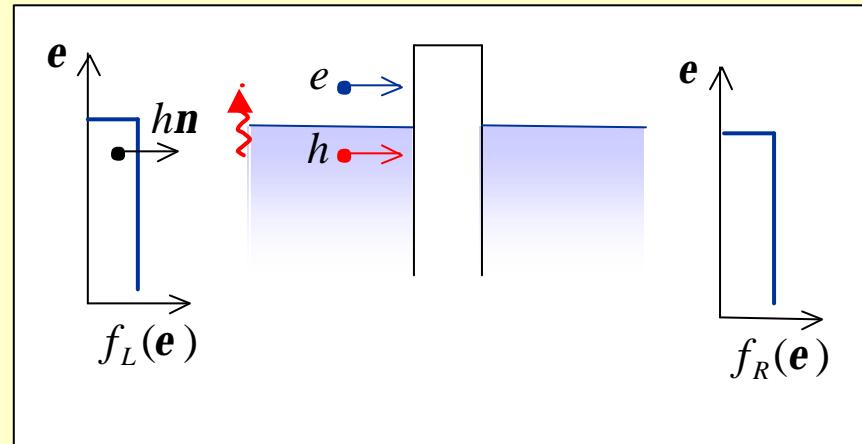


current of pumped incoming electrons :

$$I_0^{(e)} = P_1 \frac{e}{h} (h n)$$

current of pumped incoming holes :

$$I_0^{(h)} = - I_0^{(e)}$$



the associated electron and hole shot noise powers are respectively:

$$S_I^{(e)} = 2e I_0^{(e)} D (1-D) \quad \text{and} \quad S_I^{(h)} = 2e I_0^{(h)} D (1-D) = S_I^{(e)}$$

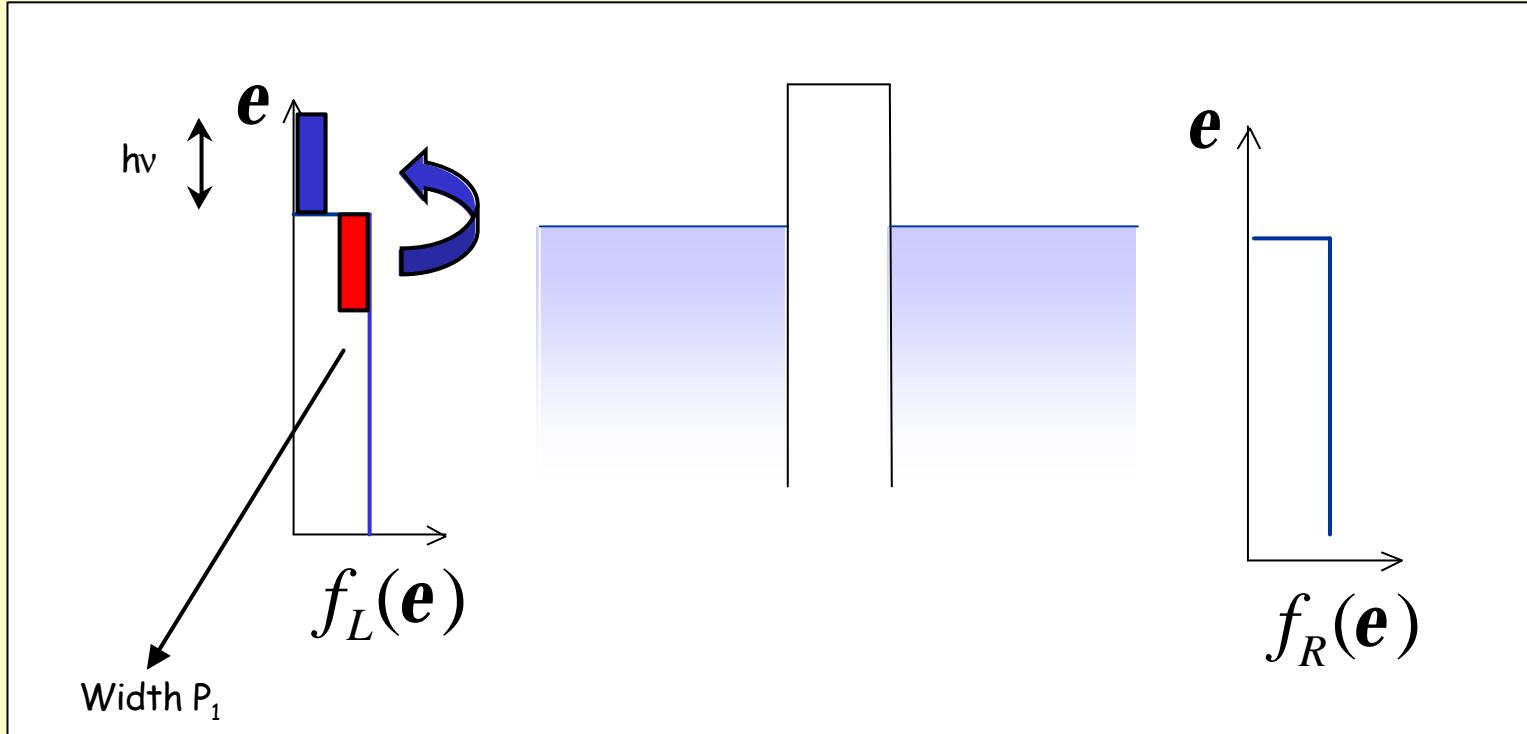
they add independently to give the electron-hole partition shot noise :

$$S_I = 4 h n \frac{e^2}{h} P_1 D (1-D)$$

while the mean current : $I = 0$

Not a simple thermal effect !

For an energy relaxation length shorter than the conductor :



$$S_I = 4h\mathbf{n} \frac{e^2}{h} \left\{ P_1 D (1 - D) + P_1 (1 - P_1) D^2 \right\}$$

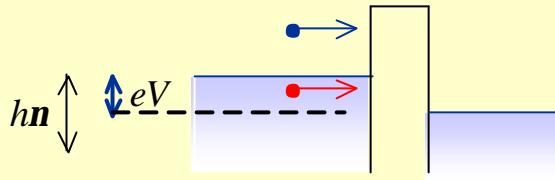
Electron hole partitioning

Occupation uncertainty

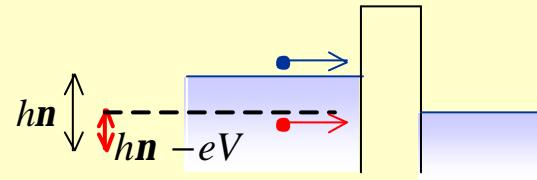
While Photon assisted process gives : $S_I = 4h\mathbf{n} \frac{e^2}{h} P_1 D (1 - D)$

Applying DC bias and RF

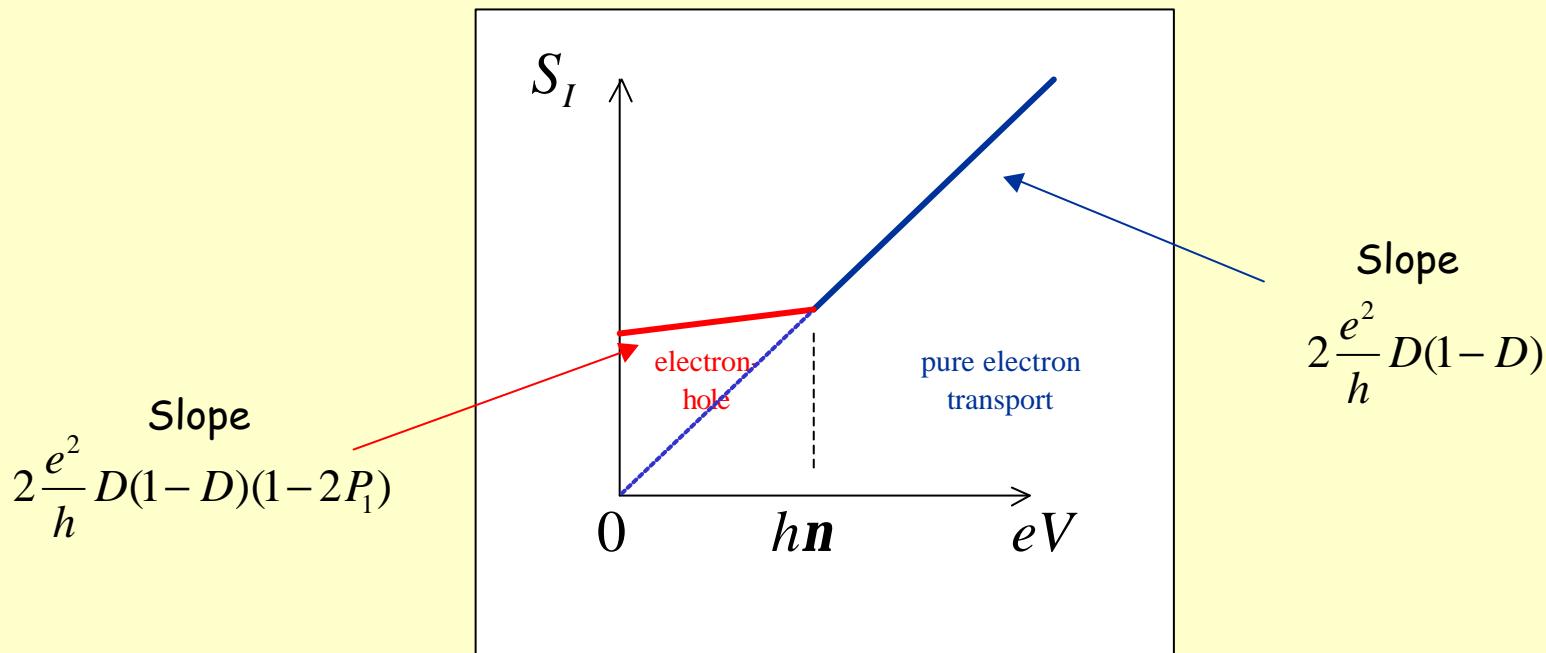
for a doubly non-equilibrium, when both a d-c voltage V and RF are applied, the slope of the transport shot noise variation with V was predicted to show a singularity at $eV = hn$



electron transport shot noise



electron-hole non-transport shot noise

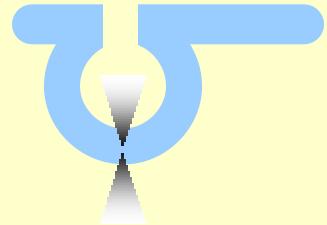


a complete formula have been derived by [Levitov and Lesovik \(PRL 94\)](#):

$f(t)$

$$S_I = 4 h n \left(\sum_l l P_l \right) \frac{e^2}{h} \sum_n D_n (1 - D_n) \quad \text{where} \quad P_l = J_l^2 (\mathbf{f}_w / \mathbf{f}_0)$$

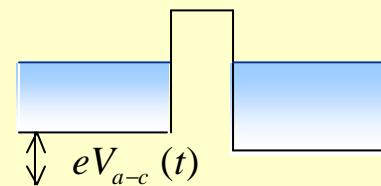
$$\mathbf{f}(t) = \mathbf{f}_w \cos \omega t \quad \text{and} \quad \mathbf{f}_0 = h/e \quad \text{"a-c Aharanov-Bohm effect"}$$



later [Pedersen et al. \(98\)](#) have considered the equivalent case of an a-c potential applied to one contact :

$$V_{a-c}(t) = V_{a-c} \cos \omega t \quad \text{with} \quad P_l = J_l^2 (eV_{a-c} / \hbar \omega)$$

$$V_{a-c}(t) = \frac{d\mathbf{f}(t)}{dt}$$



At Finite Temperature :

$$T_N = \frac{S_I}{4G k_B} = T \left(\frac{\sum_n D_n^2}{\sum_n D_n} \right) + \frac{\sum_n D_n (1 - D_n)}{\sum_n D_n} \cdot \sum_{\pm} \sum_{l=0}^{\infty} \frac{(eV \pm lhn)}{2k_B} J_l^2(\mathbf{a}) \coth \left(\frac{eV \pm lhn}{2k_B T} \right)$$

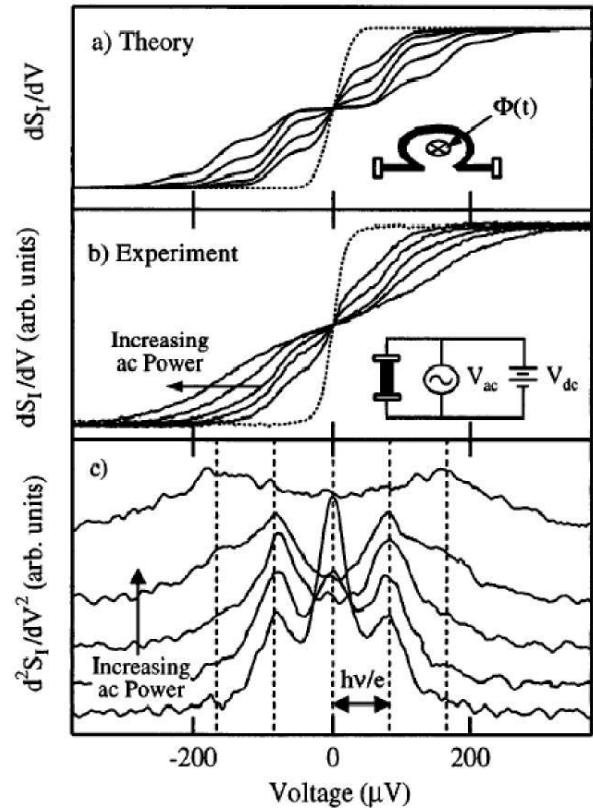
One needs $k_B T \ll \hbar v$

$17 \text{ GHz} \equiv 850 \text{ mK}$

Singularity at $eV = h\nu$

The singularity was observed by [Schoelkopf et al.](#) ([PRL 98](#)) in the doubly non-equilibrium regime (RF and V bias) using

- a **diffusive system** (and later a S-diffusive junction)
- measuring the **derivative** of the transport noise versus d-c bias voltage **V**
- they provide the first evidence of photon-assisted processes in shot noise, supporting Lesovik's model.

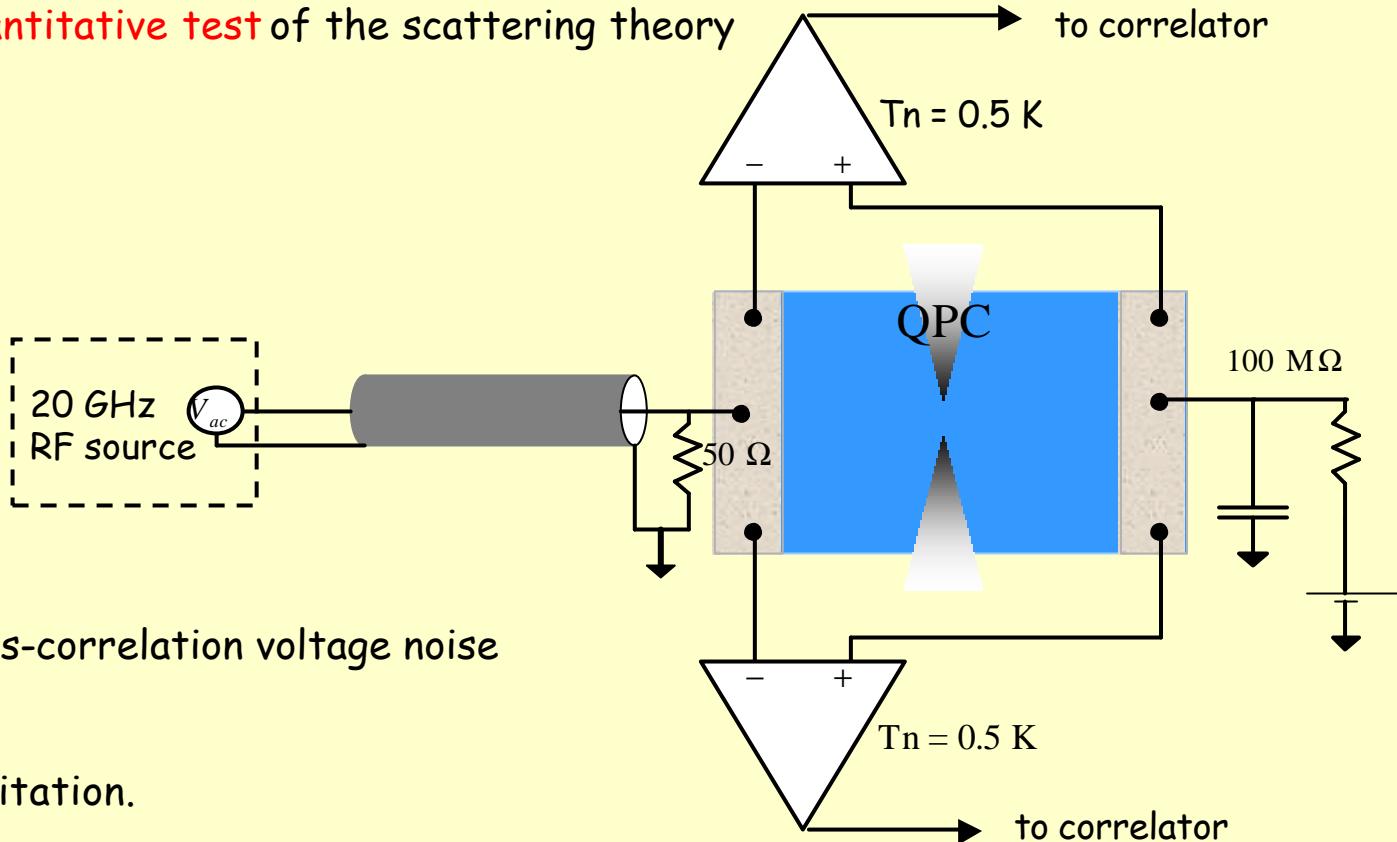


→ the Fano factor was fixed by the bimodal statistics of the transmission probabilities of a diffusive conductor:

→ no possibility to measure the total shot noise at zero bias (non-transport electron-hole pair shot noise)

$$F = \frac{\left\langle \sum_n D_n (1-D_n) \right\rangle}{\left\langle \sum_n D_n \right\rangle} = 1/3$$

- ballistic QPC to control the transmission and vary the Fano factor
- total shot noise measurements to probe the V=0 non transport electron-hole pairs shot noise
- allows for quantitative test of the scattering theory



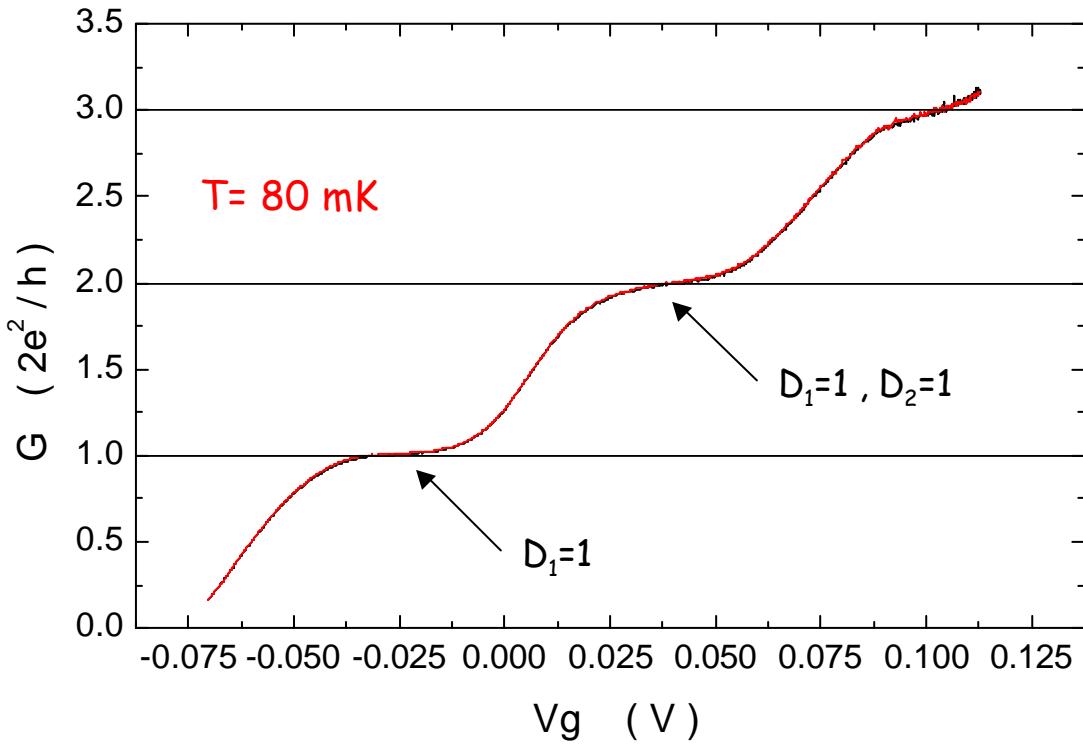
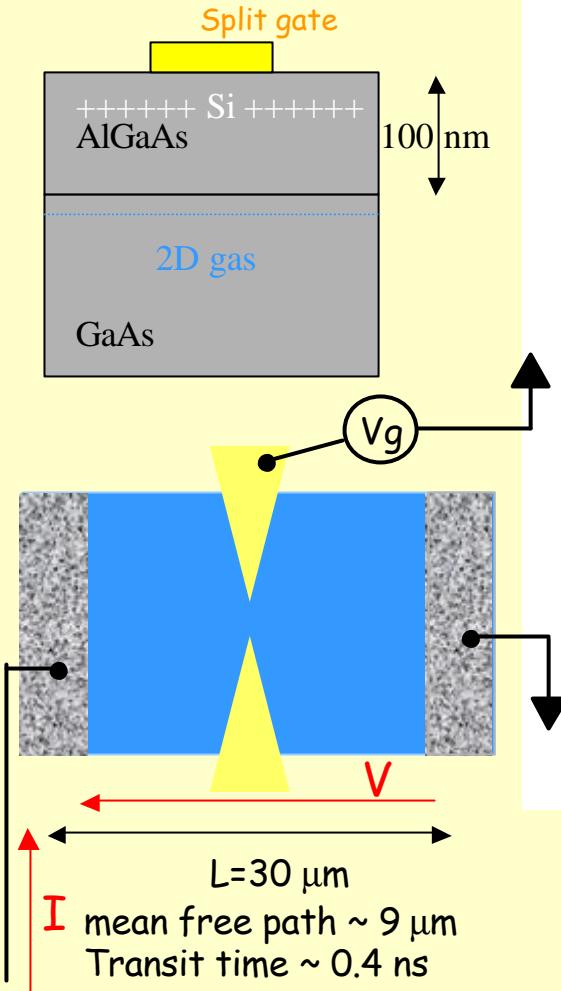
Quantum Point Contact

(tuning the transmission probability of the first two modes)

2D electron gas in GaAs/GaAlAs
 $\mu = 8 \cdot 10^5 \text{ cm}^2/\text{Vs}$
 $n_s = 4.8 \cdot 10^{11} \text{ cm}^{-2}$

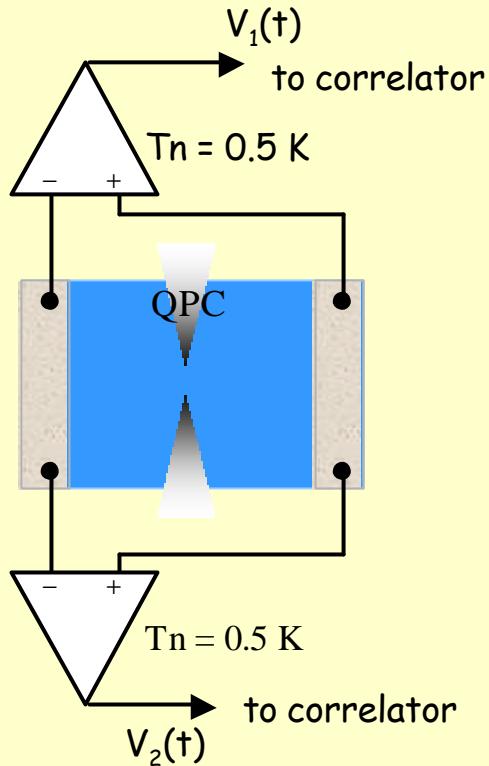
$$G = dI/dV = \frac{2e^2}{h} \sum_n D_n$$

$$h/e^2 = 25812 \Omega$$



→ Tuning of the mode transmissions

Calibration using Johnson-Nyquist Noise at D = 1

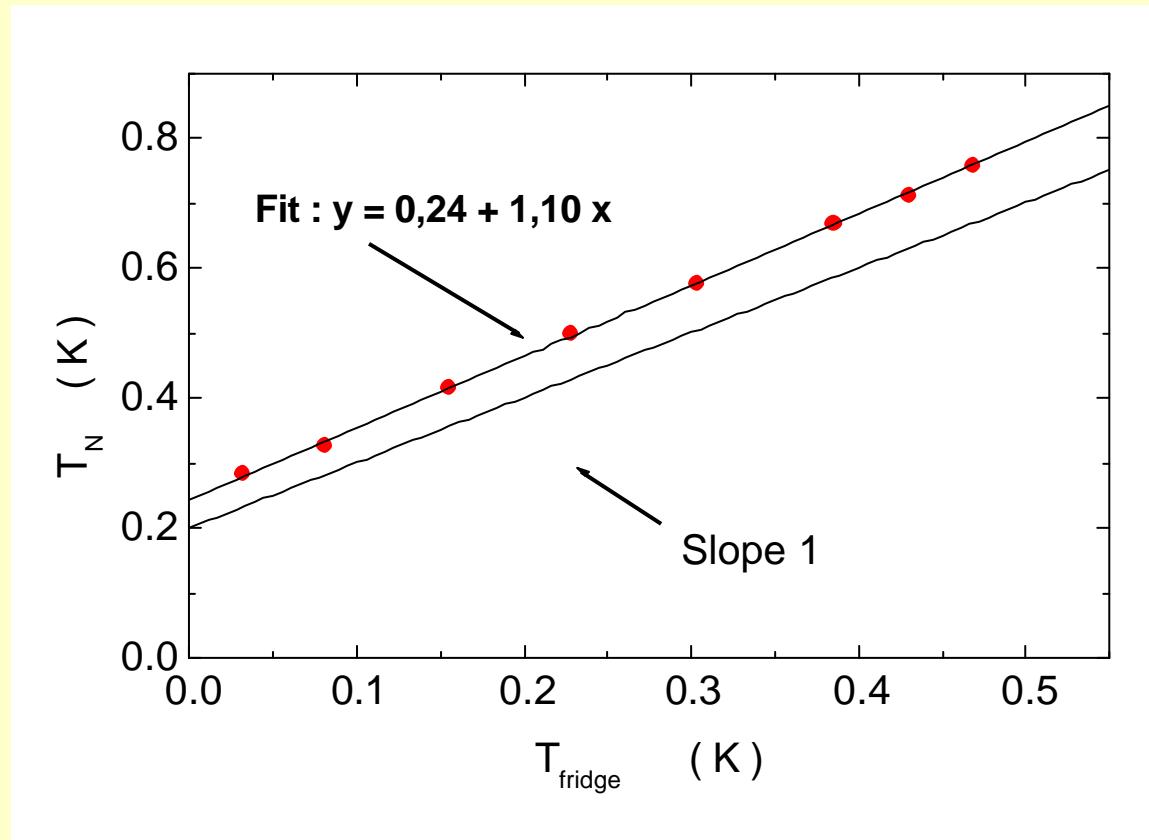


Cross correlated power spectrum

$$S_{V_1 V_2}(\omega) = \int \overline{V_1(t)V_2(t+\tau)} \cos(\omega t) dt$$

$$S_I = S_{V_1 V_2}(\omega) G^2 \quad \text{2 to 4 kHz frequency range}$$

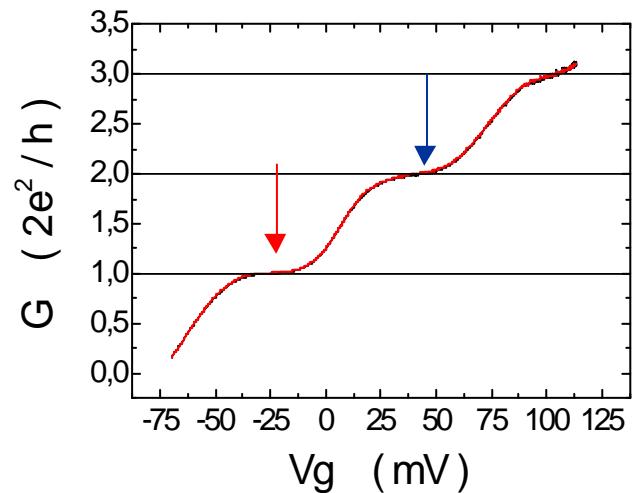
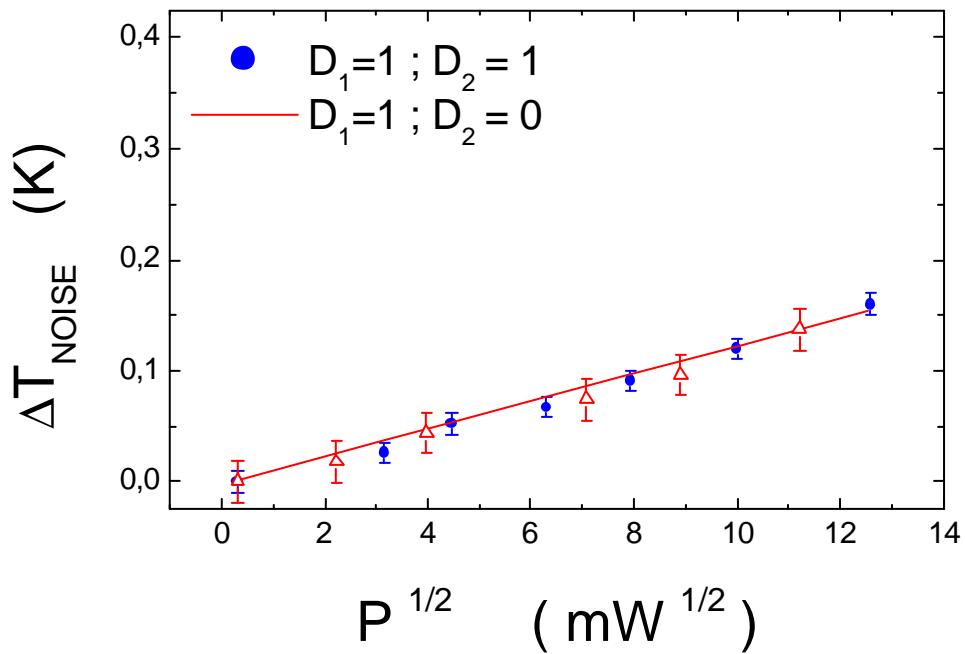
Sensitivity : 10 min. acq. time leads to 5 mK noise temperature accuracy at D = 1 (12906Ω)



$$T_N = S_I / (4k_B G)$$

1 - check for possible heating by RF power (no bias voltage, i.e. no current)

At transmission 1 or 2 no electron-hole partition noise is expected !



$$T_0 = 98 \text{ mK}$$

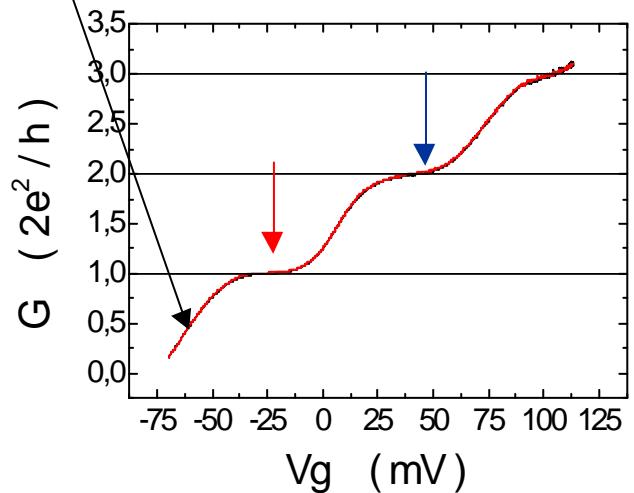
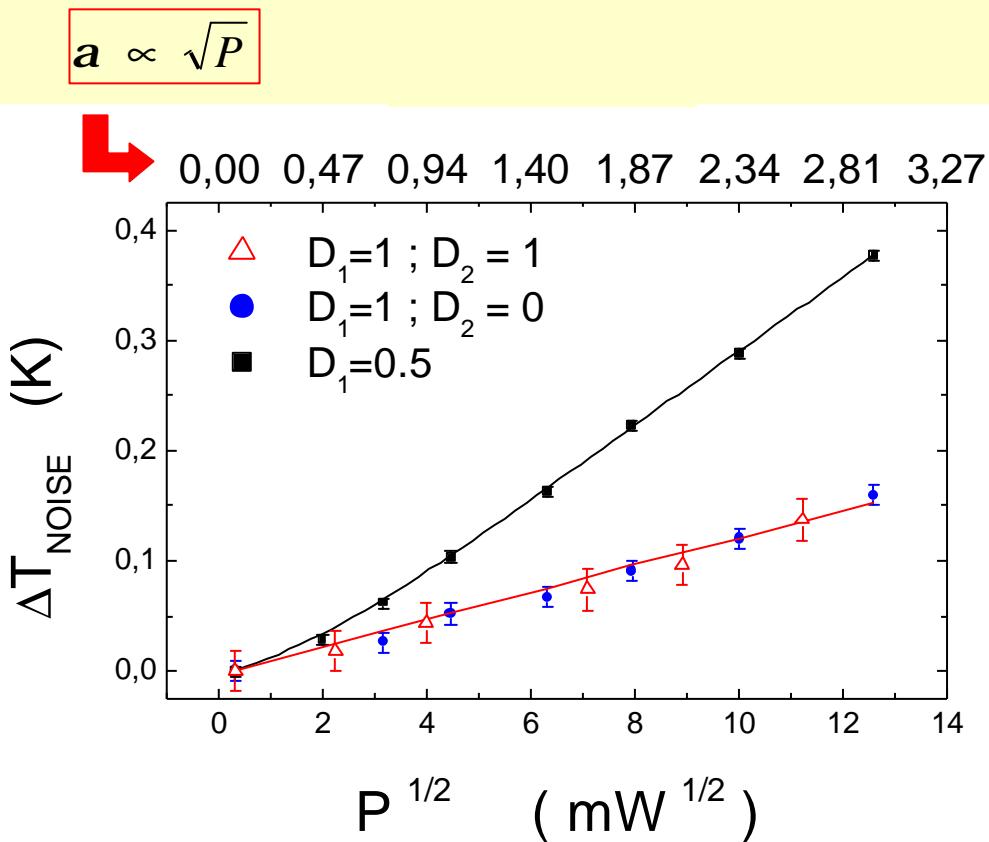
$$n = 17.32 \text{ GHz}$$



Determination of $T = T_0 + \Delta T_N$

2 - check for possible e-h partition noise at 1/2 transmission:

$$D_1 = 0.5 \quad \text{and} \quad D_{n>1} = 0$$



$$T_0 = 98 \text{ mK}$$

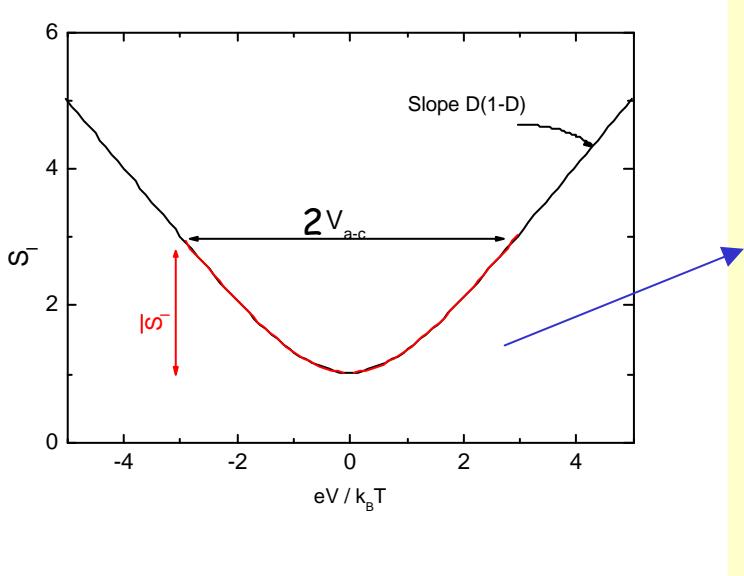
$$17.32 \text{ GHz}$$

- good fit with theory gives a calibration of $a = eV_{ac} / hn$ with RF power



Determination of the coupling parameter α

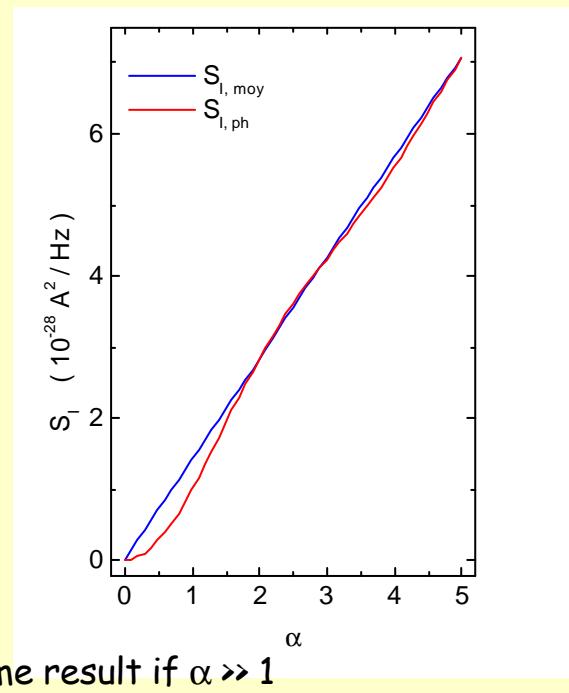
Quantum or Classical ?



$$V(t) = V_{a-c} \sin(2\mathbf{p}nt) ; \quad \mathbf{a} = eV_{a-c} / h\mathbf{n}$$

Low frequency approximation :

$$S_{I,moy} = 2e \frac{e^2}{h} \overline{V(t)} D(1-D) = 4h\mathbf{n} \frac{e^2}{h} D(1-D) \frac{\mathbf{a}}{\mathbf{p}}$$

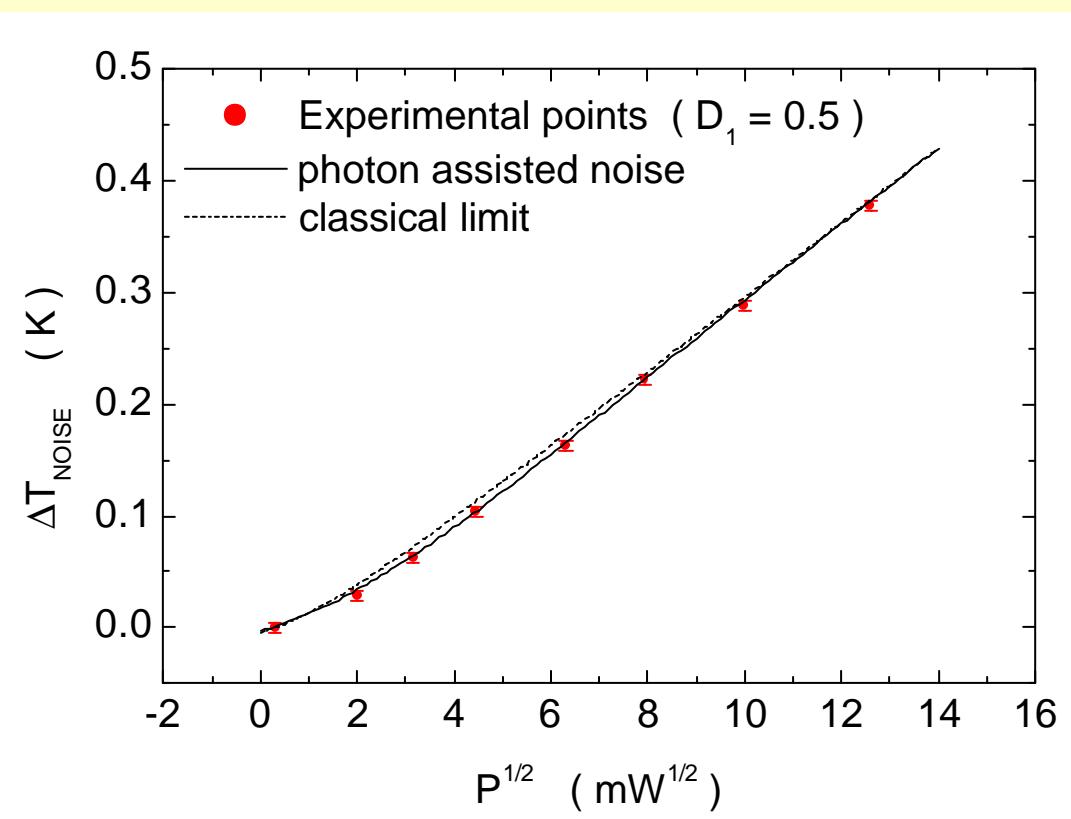


Photon assisted processes :

$$S_I = 4h\mathbf{n} \frac{e^2}{h} D(1-D) \left(\sum_l l J_l^2(\mathbf{a}) \right)$$

Same result if $\alpha \gg 1$

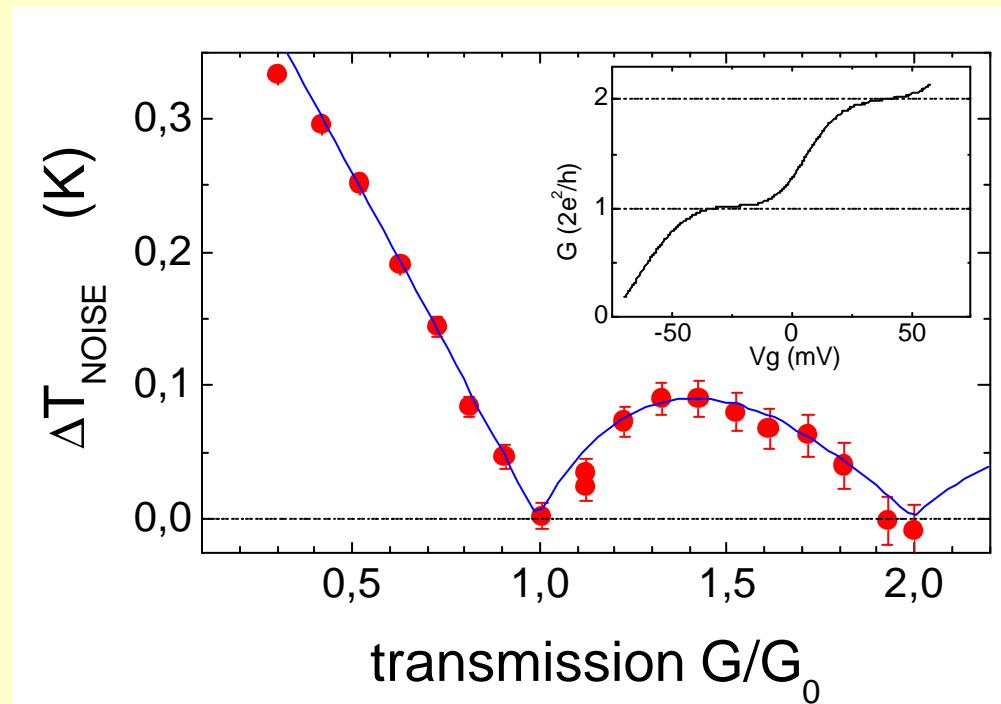
Quantum !



3 - Is this really the partition noise of photon-created electron-hole pairs ?

QPC allows to measure
the Fano factor of the
e-h partition noise

(no dc V bias, no current !)

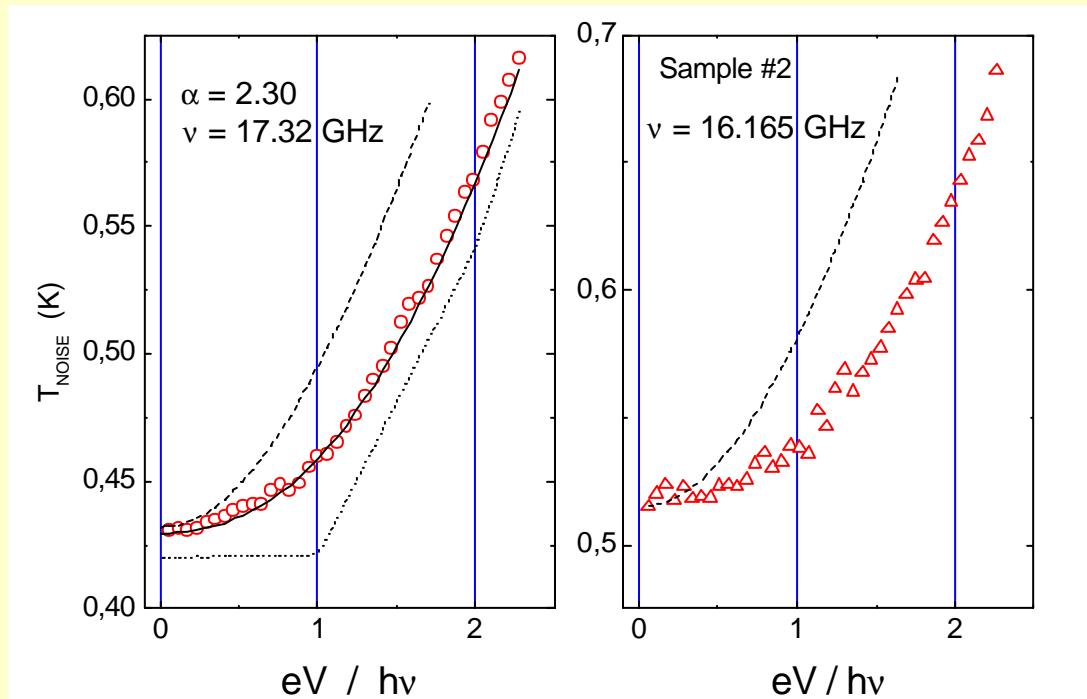


$$\frac{S_I}{4G k_B} = T \left(J_0^2(\mathbf{a}) + \frac{\sum D_n^2}{\sum D_n} (1 - J_0^2(\mathbf{a})) \right) + \boxed{\frac{h\mathbf{n}}{k_B} \left(\sum_l l J_l^2(\mathbf{a}) \right) \frac{\sum_n D_n (1 - D_n)}{\sum_n D_n}}$$

α, D_n, T are known : perfect agreement without adjustable parameter

4 - additional confirmation of photon-created e-h pairs : RF and dc voltage V

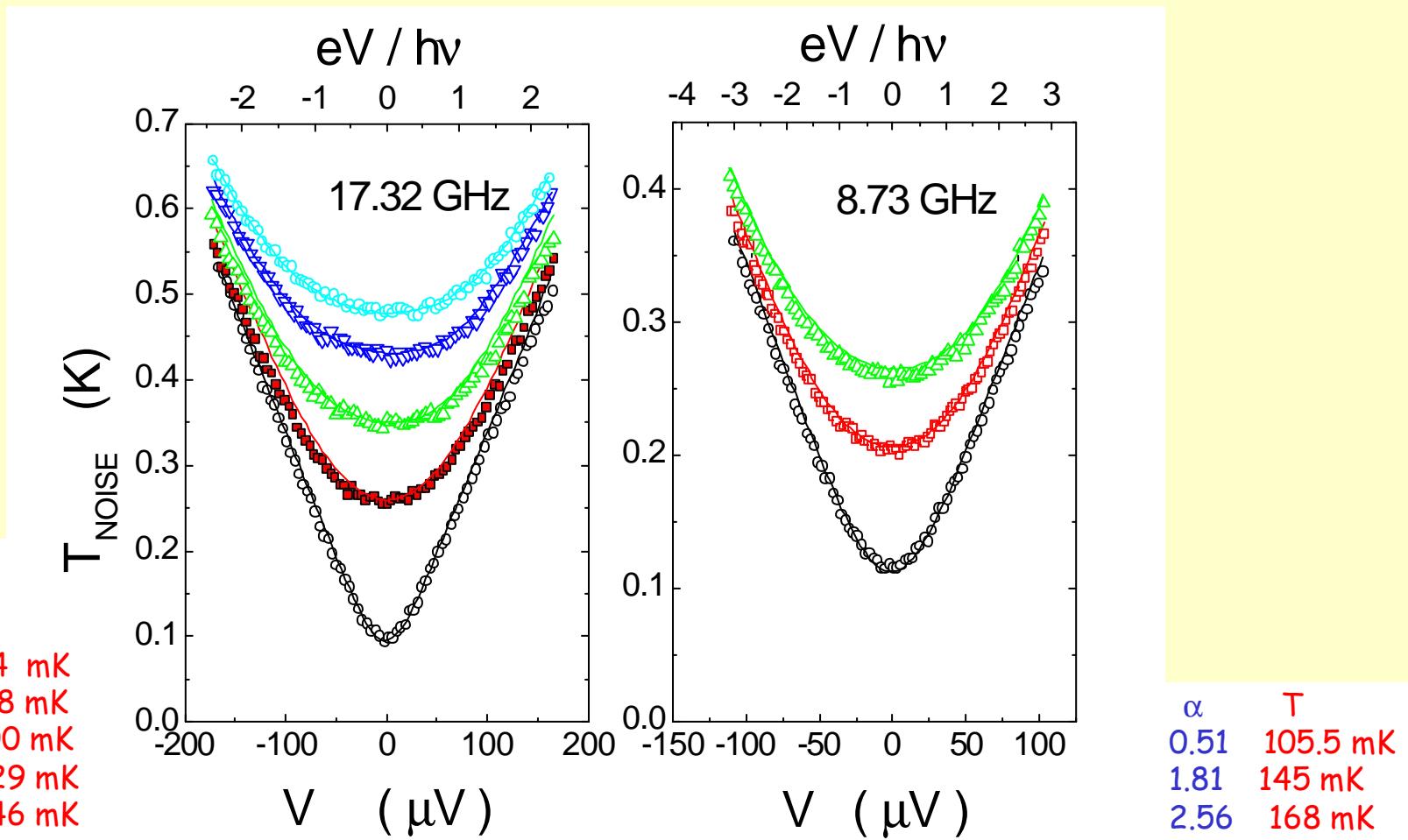
Transmission 1/2



$$T_N = \frac{S_I}{4G k_B} = T \left(\sum_n D_n^2 \right) + \frac{\sum_n D_n (1-D_n)}{\sum_n D_n} \cdot \sum_{\pm} \sum_{l=0}^{\infty} \frac{(eV \pm l\hbar\nu)}{2k_B} J_1^2(\mathbf{a}) \coth \left(\frac{eV \pm l\hbar\nu}{2k_B T} \right)$$

α, D_n, T are known : perfect agreement without adjustable parameter

5 - transmission 1/2 , various rf power (or α), two different frequencies



(no fits, just comparison data / theory)

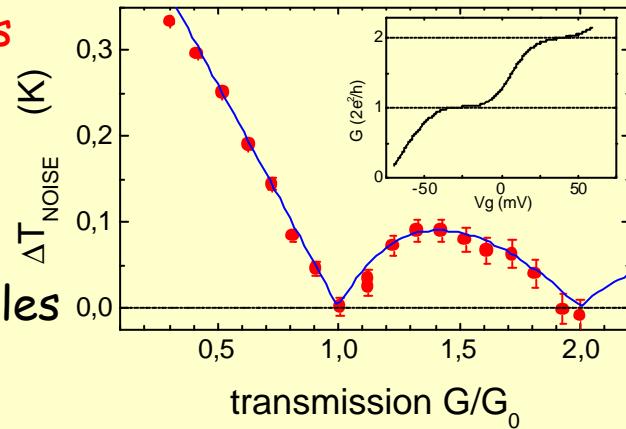
→ quantitative test of quantum scattering model of photo-assisted shot noise

CONCLUSION

partition noise of photo-created Electron-hole pairs
(non-transport Shot Noise)

the Fano factor has been accurately measured

radiofrequency provide a new way to probe q-particles
without necessary transport



at finite dc voltage and under various transmissions
and r-f powers we have made an accurate test of
the photon-assisted shot noise scattering theory

